

ABSTRACT

A semiconductor device includes an active pattern extending along a first direction, and first and second word lines intersecting the active pattern. The active pattern includes a center active portion between the first and second word lines. The center active portion includes a center portion extending from the first word line to the second word line, a first center protrusion protruding from one side surface of the center portion in a second direction intersecting the first direction, and a second center protrusion protruding from another side surface of the center portion in an opposite direction to the second direction. The first center protrusion extends from the first word line along the first direction. The second center protrusion extends from the second word line along an opposite direction to the first direction.

FIG. 3B